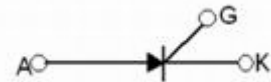
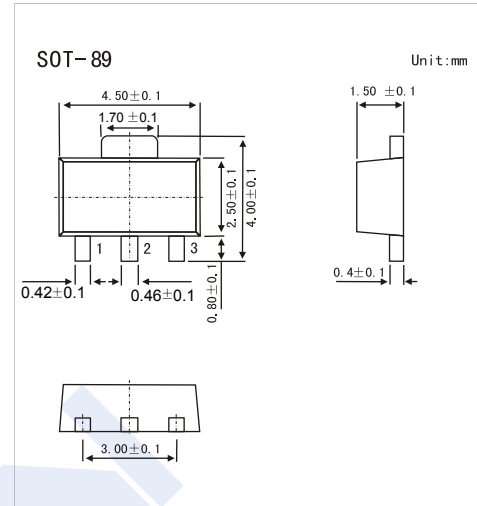


Silicon Controlled Rectifier

MCR100 (KCR100)

■ Features

- Current- I_{GT} : 200 μ A
- I_{TRMS} : 0.8 A.
- V_{RRM}/V_{DRM} : MCR100-6: 400 V
MCR100-6R: 400 V
MCR100-8: 600 V
MCR100-8R: 600 V
- Operating and storage junction temperature range
- T_J, T_{stg} : -55°C to +150°C

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
On State Voltage (Note.1)	V_{TM}	$I_{TM} = 1 \text{ A}$			1.7	V
Gate Trigger Voltage	V_{GT}	$V_{AK} = 7 \text{ V}$			0.8	
Peak Repetitive forward and reverse blocking voltage	V_{DRM} V_{RRM}	$I_{DRM} = 10 \mu\text{A}$	400 600			
Holding current	I_H	$V_{AK} = 7 \text{ V}, I_H = 20 \text{ mA}$			5	mA
Peak forward or reverse blocking Current	I_{DRM} I_{RRM}	$V_{AK} = \text{Rated}$ V_{DRM} or V_{RRM}			10	uA
Gate trigger current	I_{GT}	A2		5	15	
		A1		15	30	
		A	$V_{AK} = 7 \text{ V}$	30	80	
		B		80	200	

Note.1: Forward current applied for 1 ms maximum duration, duty cycle $\leq 1\%$

■ Ordering information

Normal	Pin Assignment			Marking
	1	2	3	
MCR100-6	G	A	K	P2*
MCR100-6R	K	A	G	P2*
MCR100-8	G	A	K	P3*
MCR100-8R	K	A	G	P3*